

Amendments to the Specification

Please replace the paragraph on page 7 of the specification, beginning on line 22, with the following new paragraph:

For an SiC support 1 ~~on~~ an siC, 6H and 4H polytype SiC epitaxy was conducted on thin 6H and 4H polytype layers 3 respectively at a temperature of 1450°C to 1550°C. 3C polytype SiC epitaxy was also conducted on a thin 3C polytype layer 3 from 1350°C. These epitaxially grown layers are referenced 4 in figure 1.